

FIG. 1A is a schematic diagram of a device for measuring the thickness of a material. The device includes a probe 12, a sensor 10, and a display 14. The probe 12 is used to measure the thickness of a material 11. The sensor 10 is connected to the probe 12 and the display 14. The display 14 shows the measured thickness of the material 11.

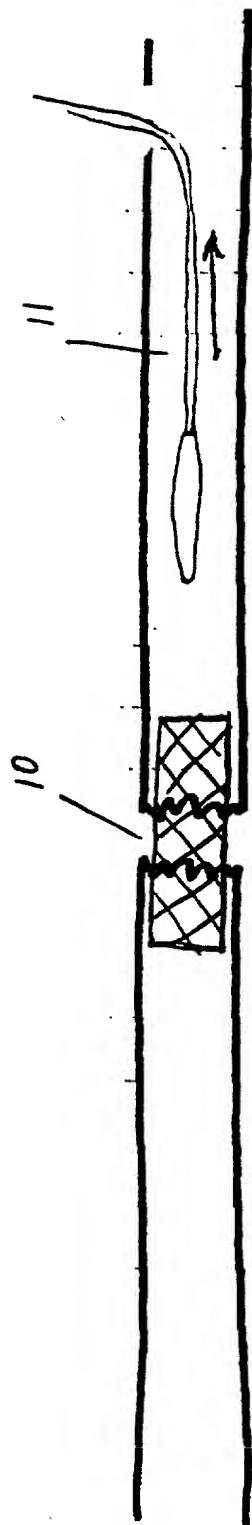
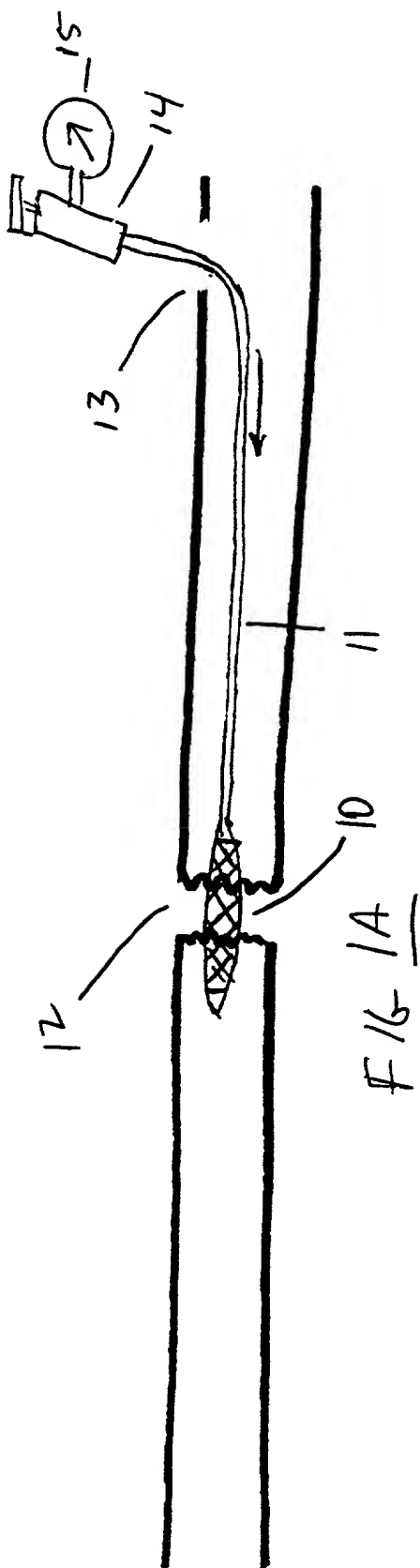


FIG. 1B

FIG. 1
FIG. 2
FIG. 3
FIG. 4
FIG. 5
FIG. 6
FIG. 7
FIG. 8
FIG. 9
FIG. 10
FIG. 11
FIG. 12
FIG. 13
FIG. 14
FIG. 15
FIG. 16
FIG. 17
FIG. 18
FIG. 19
FIG. 20
FIG. 21
FIG. 22
FIG. 23
FIG. 24
FIG. 25
FIG. 26
FIG. 27
FIG. 28
FIG. 29
FIG. 30
FIG. 31
FIG. 32
FIG. 33
FIG. 34
FIG. 35
FIG. 36
FIG. 37
FIG. 38
FIG. 39
FIG. 40
FIG. 41
FIG. 42
FIG. 43
FIG. 44
FIG. 45
FIG. 46
FIG. 47
FIG. 48
FIG. 49
FIG. 50
FIG. 51
FIG. 52
FIG. 53
FIG. 54
FIG. 55
FIG. 56
FIG. 57
FIG. 58
FIG. 59
FIG. 60
FIG. 61
FIG. 62
FIG. 63
FIG. 64
FIG. 65
FIG. 66
FIG. 67
FIG. 68
FIG. 69
FIG. 70
FIG. 71
FIG. 72
FIG. 73
FIG. 74
FIG. 75
FIG. 76
FIG. 77
FIG. 78
FIG. 79
FIG. 80
FIG. 81
FIG. 82
FIG. 83
FIG. 84
FIG. 85
FIG. 86
FIG. 87
FIG. 88
FIG. 89
FIG. 90
FIG. 91
FIG. 92
FIG. 93
FIG. 94
FIG. 95
FIG. 96
FIG. 97
FIG. 98
FIG. 99
FIG. 100

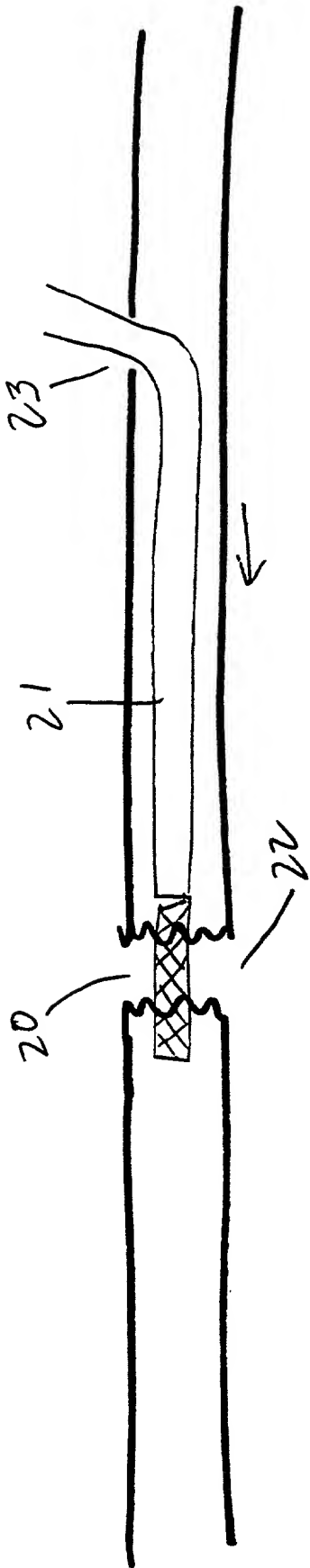


FIG 2A

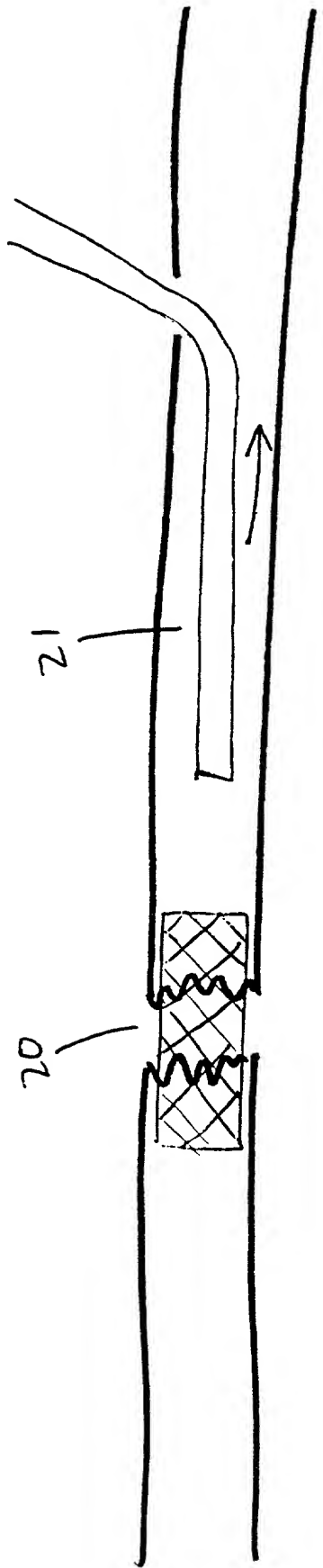


FIG- 2B

FIG. 3A is a cross-sectional view of a device in a first state, showing a central region 30 and a surrounding region 31.

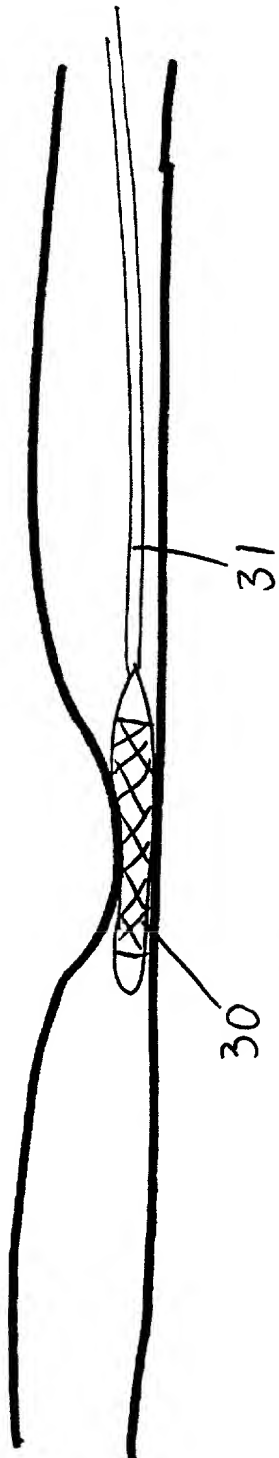


FIG 3A

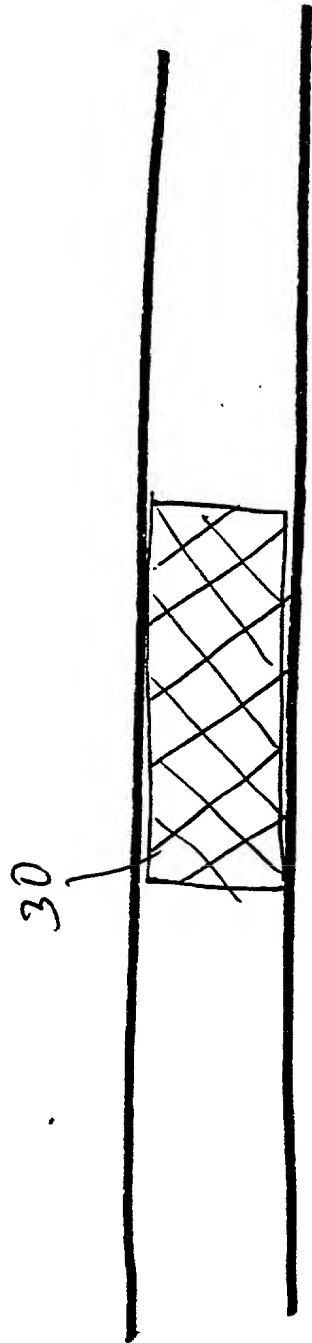
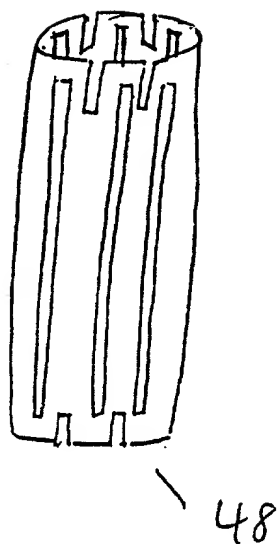
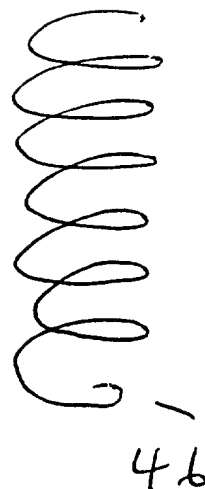
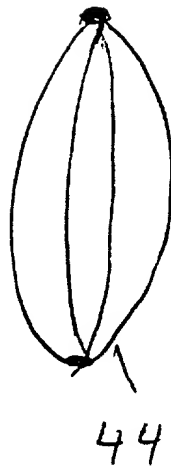
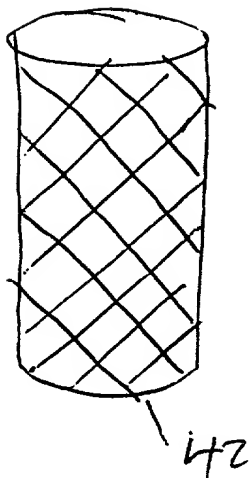


FIG 3B



kegel
sinusoid
wanderung

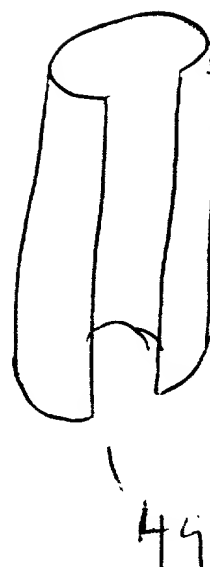


FIG 4

FIG 5A

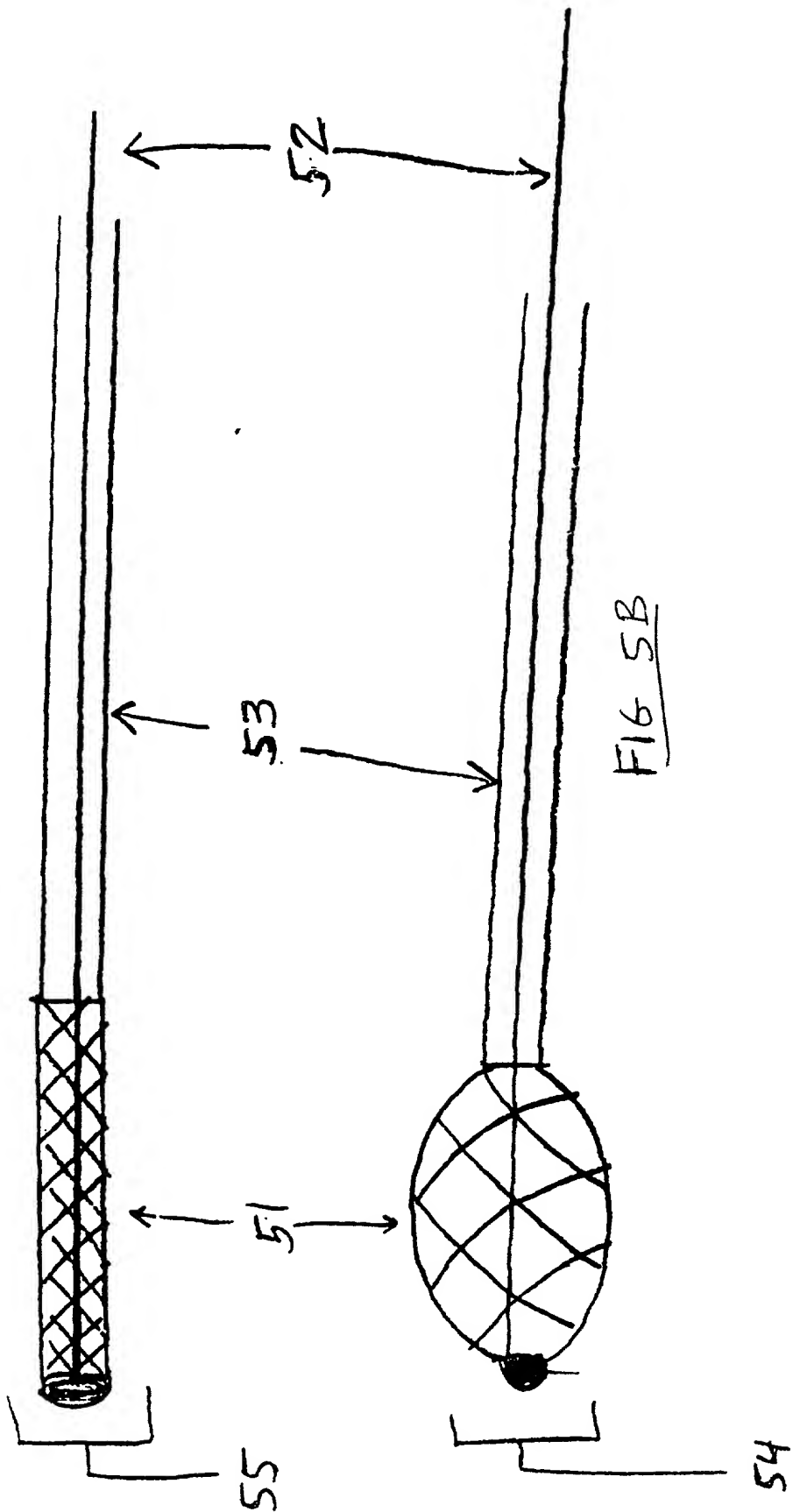


FIG 5

FIG. 10 is a perspective view of the device of FIG. 9, showing the device in a closed position. The device is shown in a perspective view, and the components are labeled with reference numerals. The device is shown in a closed position, and the components are labeled with reference numerals. The device is shown in a perspective view, and the components are labeled with reference numerals. The device is shown in a closed position, and the components are labeled with reference numerals.

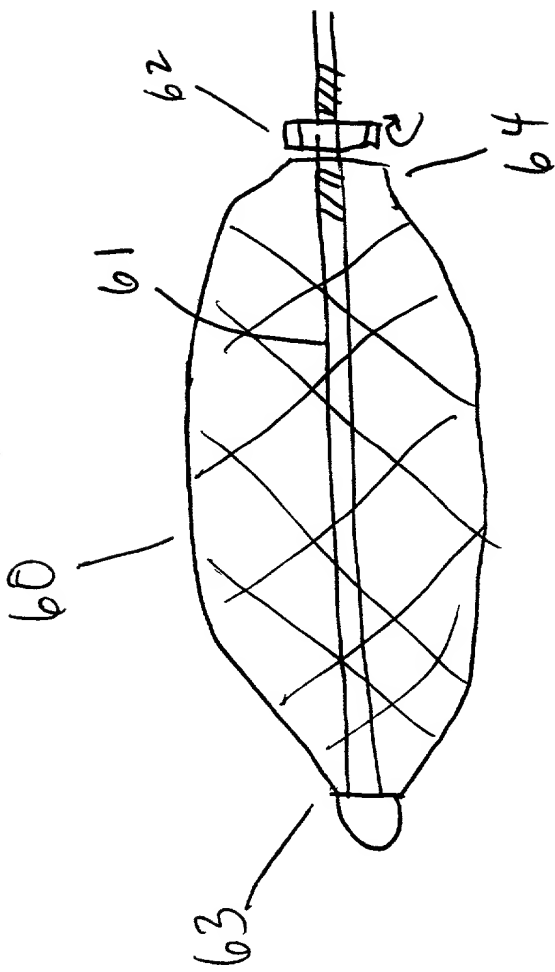


Fig 10

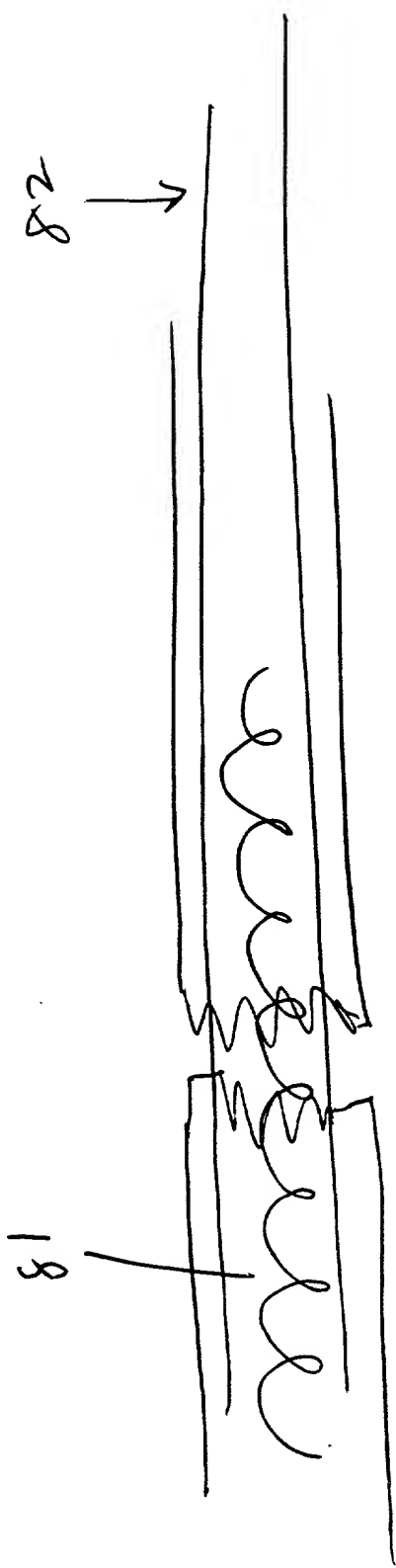


FIG 8A

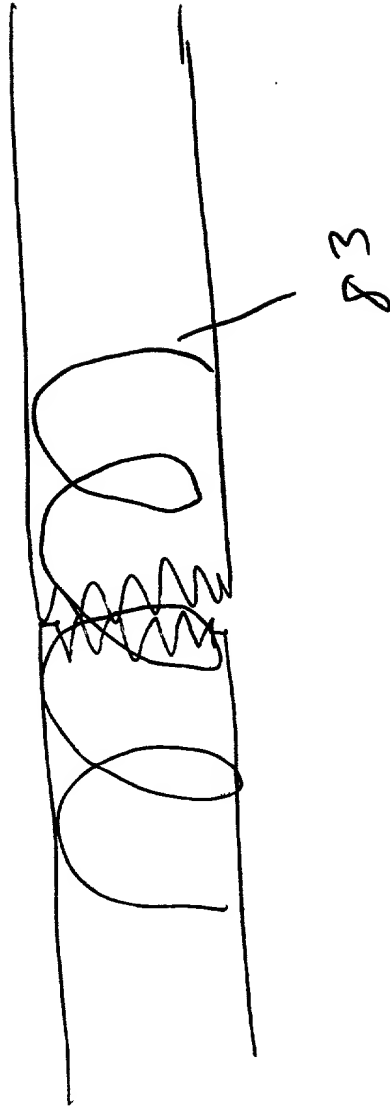
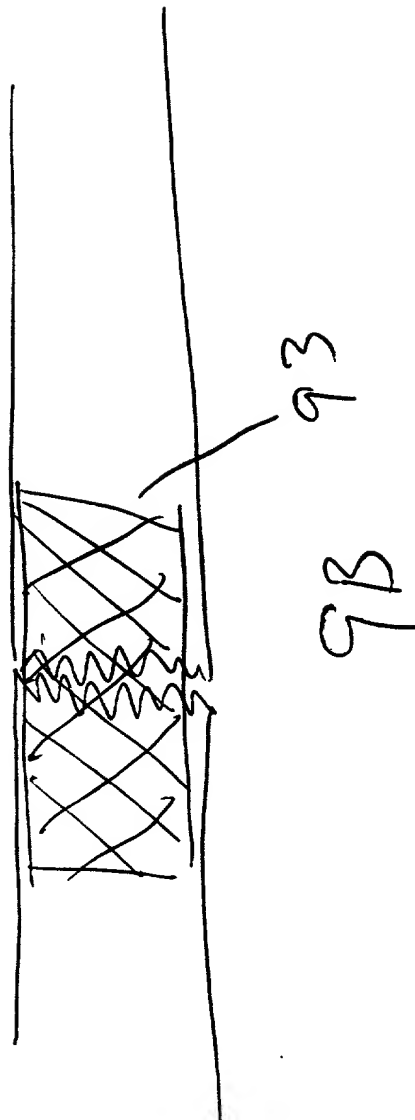


FIG 8B

FIG. 9A is a cross-sectional view of a device 90, showing a substrate 91, a layer 92, and a layer 93. The layer 92 is a conductive layer, and the layer 93 is a dielectric layer. The device 90 is a thin-film transistor (TFT) structure.



9A



9B

FIG. 10 is a schematic diagram of a device 100, showing a rectangular frame 101 with a spring 102 inside. The frame 101 is connected to a support 103. The spring 102 is connected to the support 103. The device 100 is shown in a cross-sectional view.

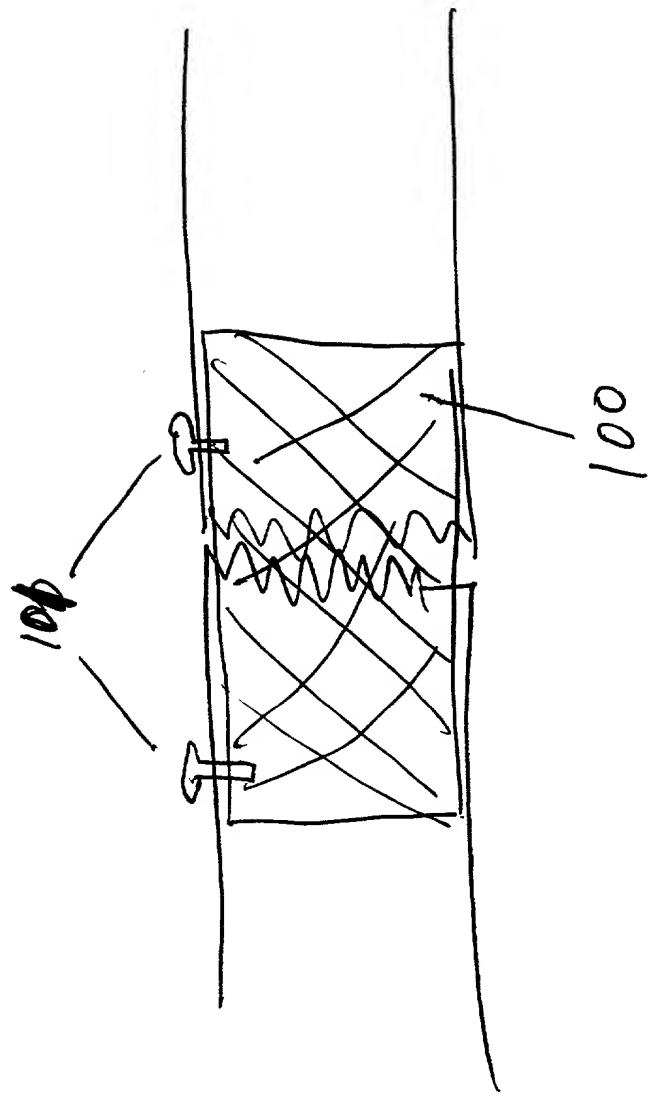


Fig. 10

FIG. 11 is a perspective view of the device of FIG. 10, showing the device in a closed position. The device is shown in a perspective view, and the components are labeled with the same reference numerals as in FIG. 10. The device is shown in a closed position, and the components are labeled with the same reference numerals as in FIG. 10.

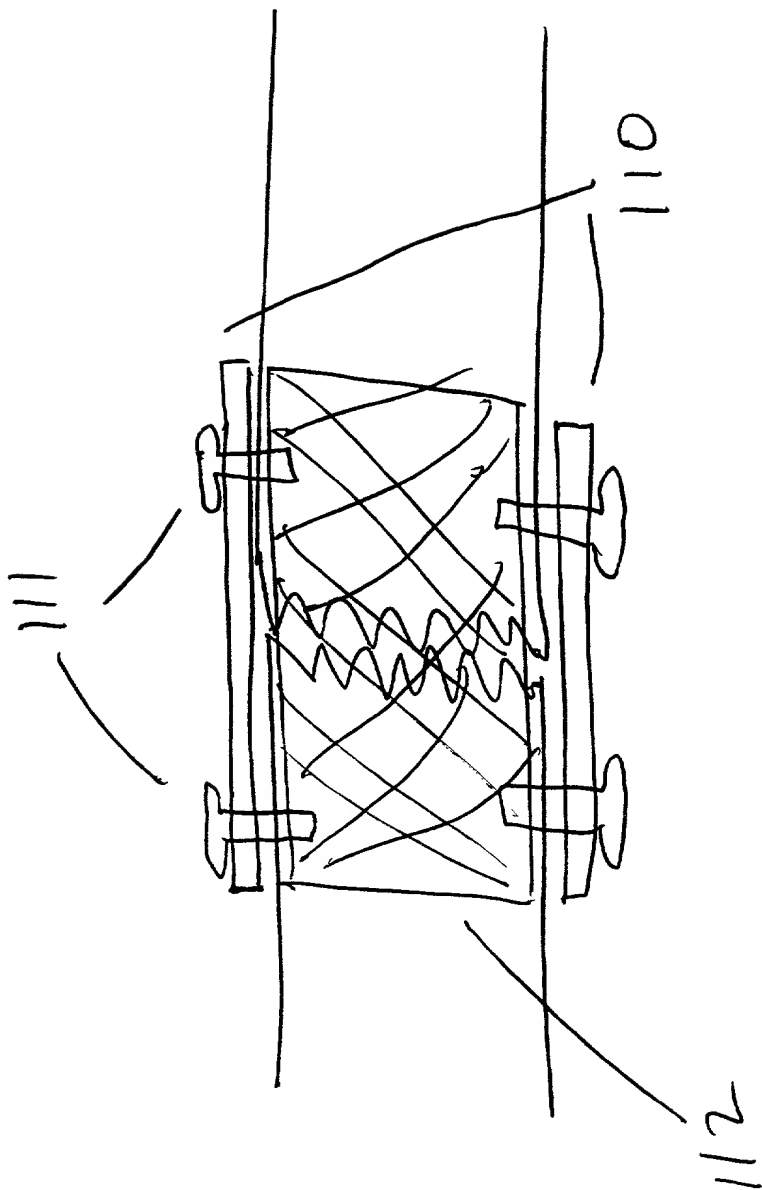


Fig 11

FIG. 12A is a schematic diagram of a device 120. The device 120 includes a substrate 121, a first layer 122, and a second layer 123. The first layer 122 is disposed on the substrate 121, and the second layer 123 is disposed on the first layer 122. The second layer 123 includes a patterned layer 124.

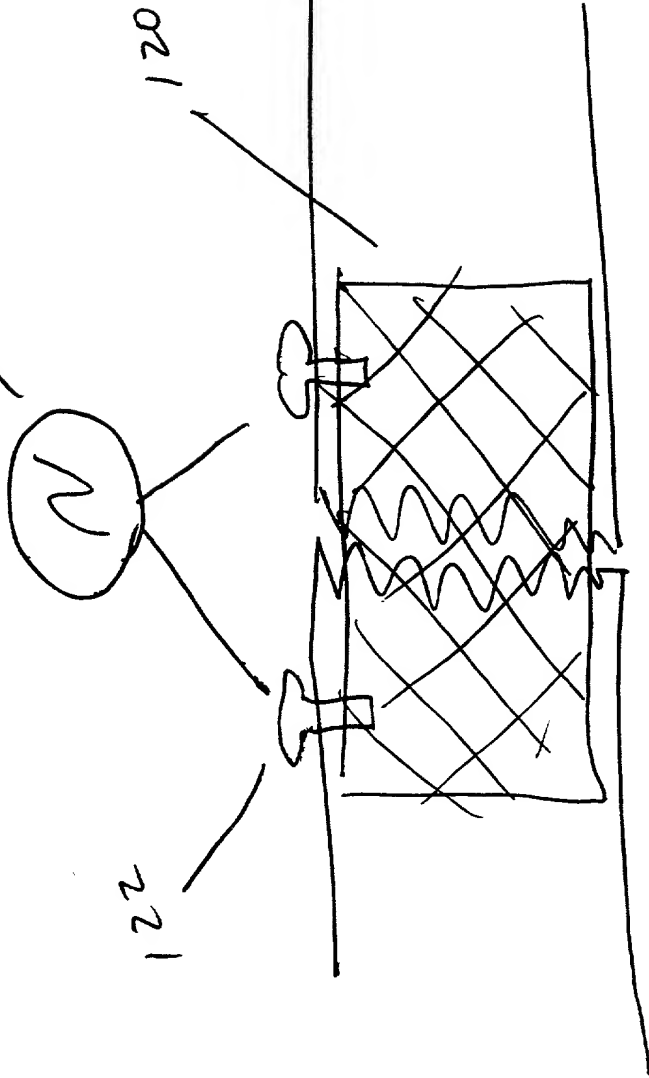


FIG. 12A

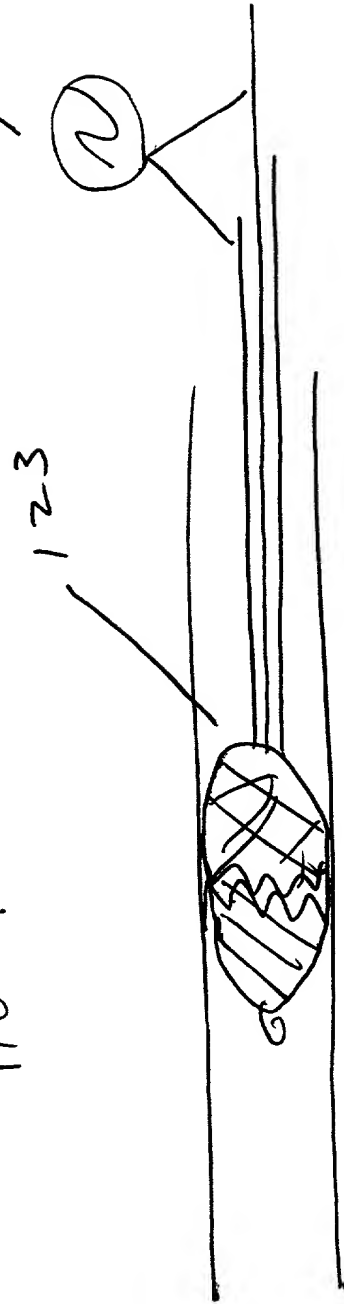


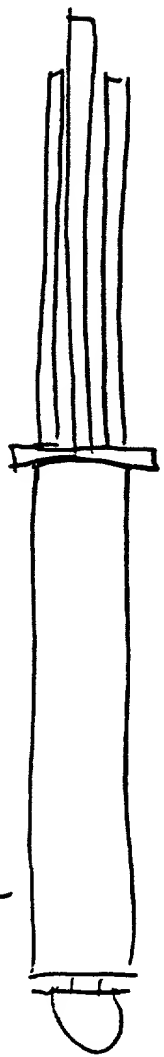
FIG. 12B



THE UNIVERSITY OF MICHIGAN LIBRARY

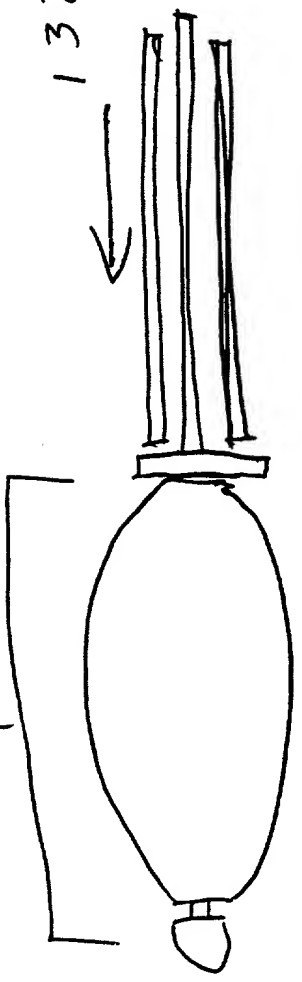
131

130



133

132



F16 13